

**DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	75mΩ @ V <sub>GS</sub> = -4.5V	-3.8A
	137mΩ @ V <sub>GS</sub> = -2.5V	-3.0A

**Description**

This MOSFET is designed to minimize on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

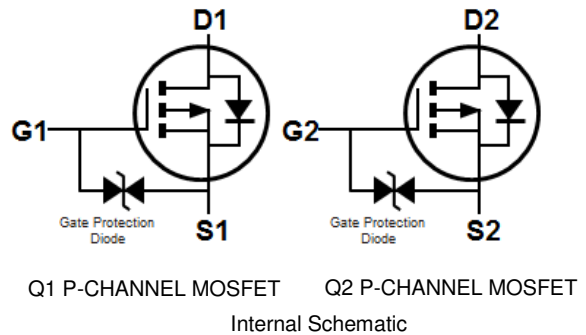
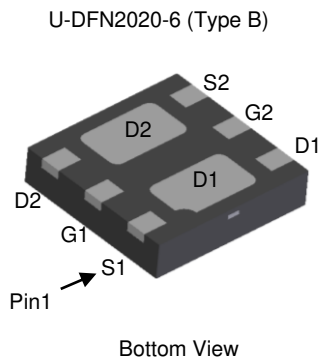
- Load Switch
- Power Management Functions
- Portable Power Adaptors

**Features**

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

**Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)


**Ordering Information** (Note 4)

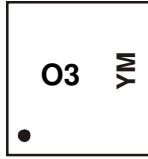
Part Number	Case	Packaging
DMP2075UFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2075UFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**

Site 1

U-DFN2020-6 (Type B)

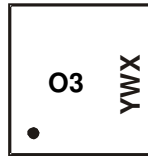


O3 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

<b>Year</b>	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	E	...	H	I	J	K	L	M	N	O	P	R
<b>Month</b>	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
<b>Code</b>	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



O3 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

<b>Year</b>	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	7	...	0	1	2	3	4	5	6	7	8	9

<b>Week</b>	1-26	27-52	53
<b>Code</b>	A-Z	a-z	z

<b>Internal Code</b>	Sun	Mon	Tue	Wed	Thu	Fri	Sat
<b>Code</b>	T	U	V	W	X	Y	Z

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±8	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	Steady State	T <sub>A</sub> = +25°C	-3.8	A
			T <sub>A</sub> = +70°C	-3.0	
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	-1.0	A		
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-25	A		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	-13	A		
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	8.5	mJ		

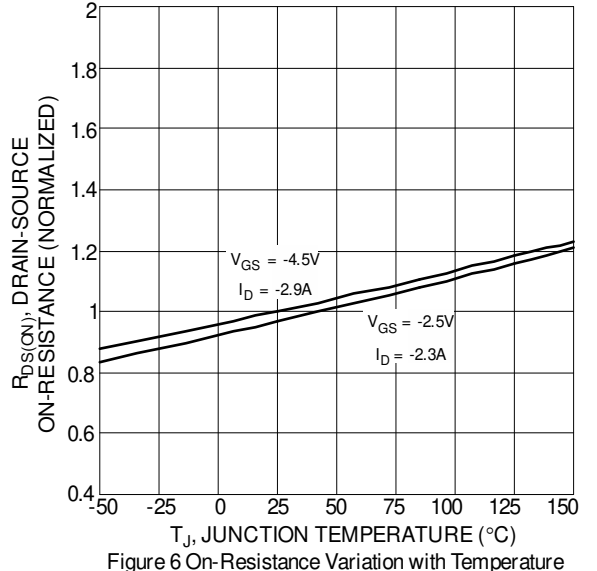
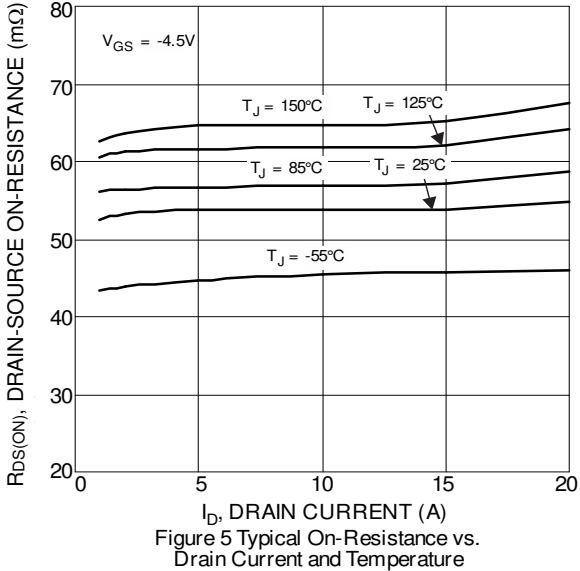
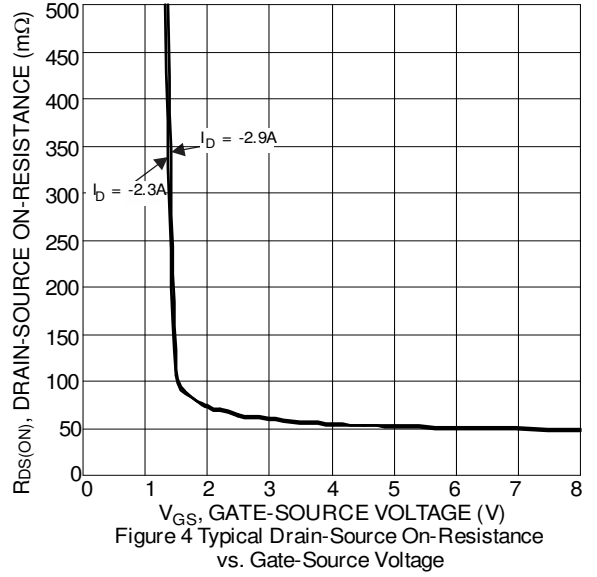
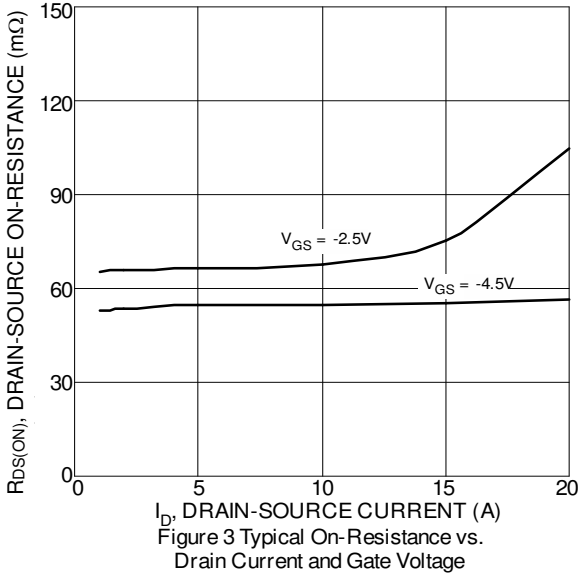
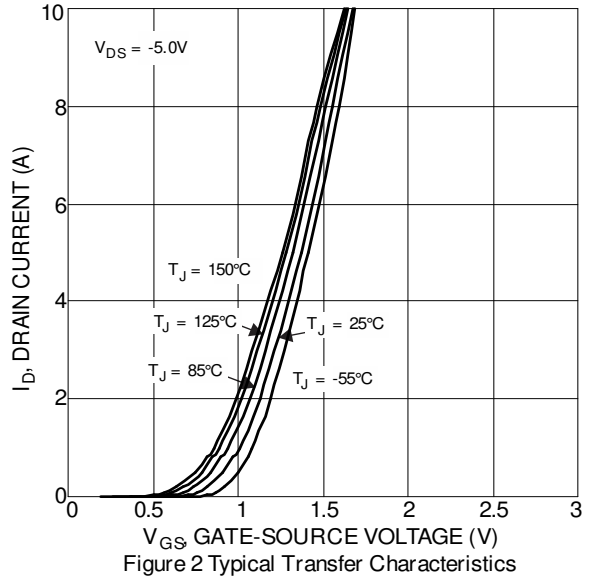
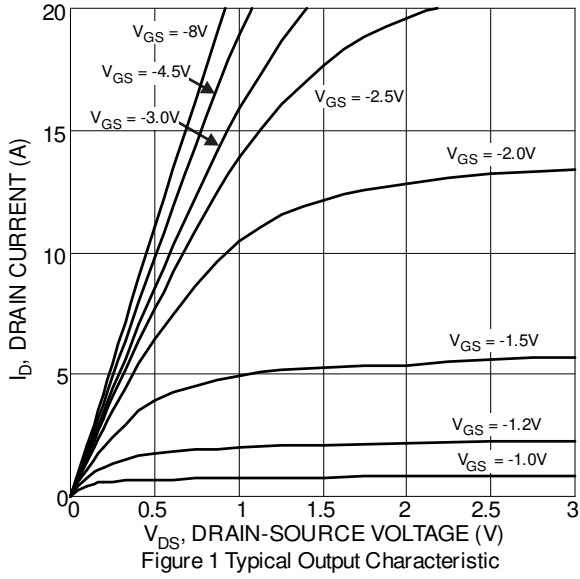
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R <sub>θJA</sub>	178
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R <sub>θJA</sub>	92
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	22		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±6.4V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.35	—	-1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	53	75	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9A
		—	64	137		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.3A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.0A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	642	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	98	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	87	—	pF	
Gate Resistance	R <sub>g</sub>	—	26.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	8.8	—	nC	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.7A
Total Gate Charge (V <sub>GS</sub> = -8V)		—	15	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	2.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.5	—	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 3.3Ω, R <sub>g</sub> = 1Ω
Turn-On Rise Time	t <sub>R</sub>	—	22.6	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	34.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	34.3	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	13	—	ns	I <sub>S</sub> = -3.0A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	3.3	—	nC	I <sub>S</sub> = -3.0A, dI/dt = 100A/μs

- Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided  
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.  
7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.  
8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.



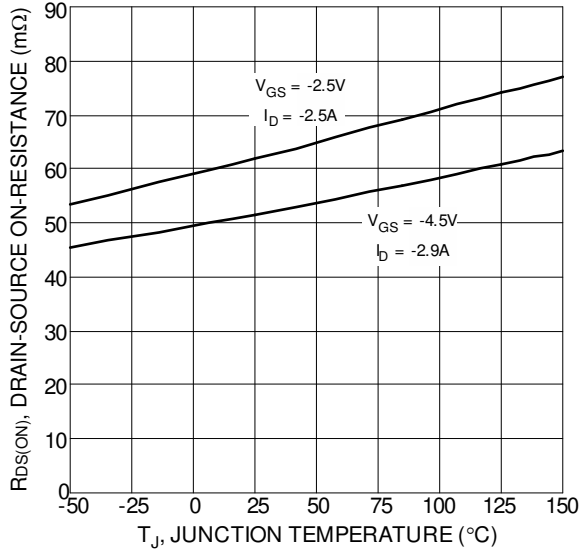


Figure 7 On-Resistance Variation with Temperature

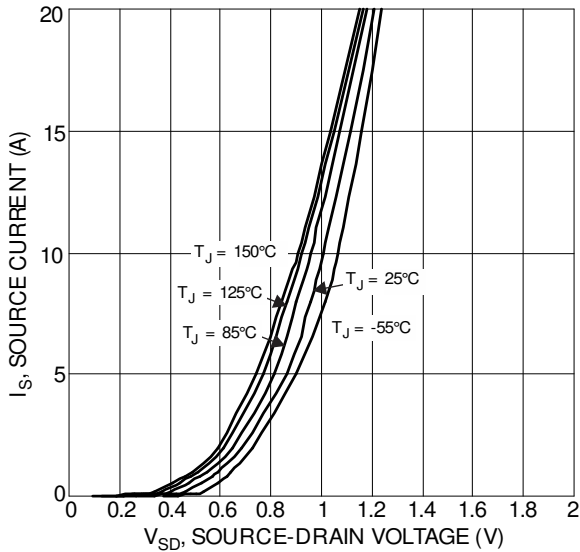


Figure 9 Diode Forward Voltage vs. Current

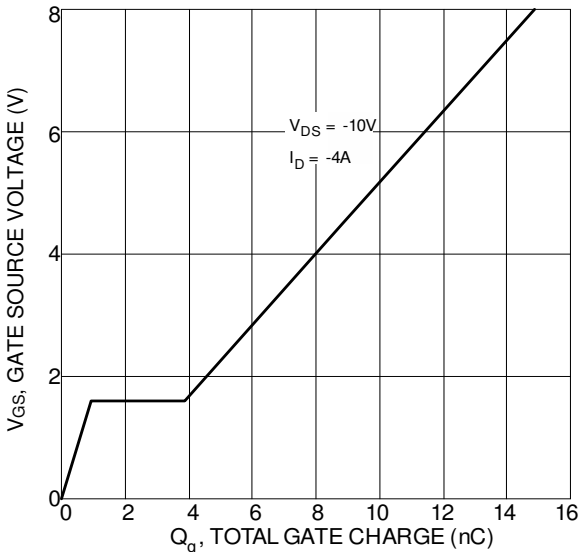


Figure 11 Gate Charge

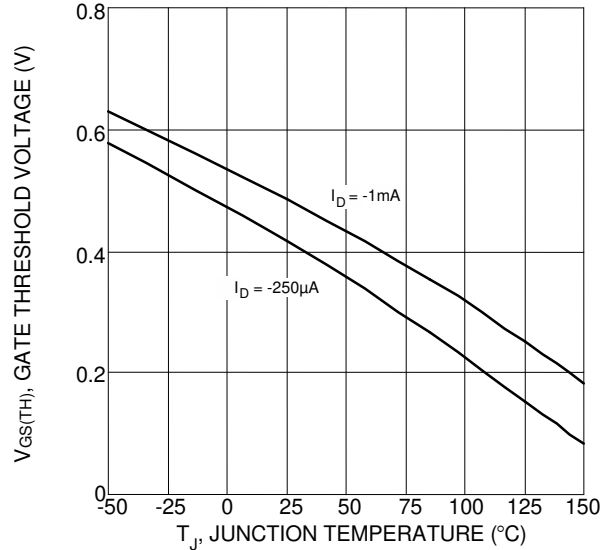


Figure 8 Gate Threshold Variation vs. Junction Temperature

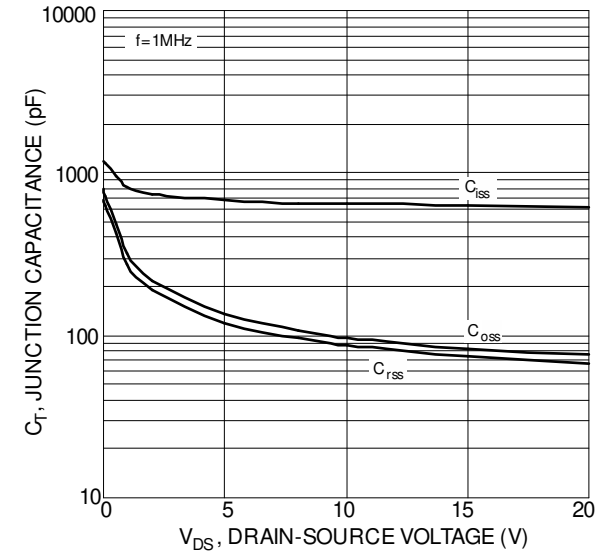


Figure 10 Typical Junction Capacitance

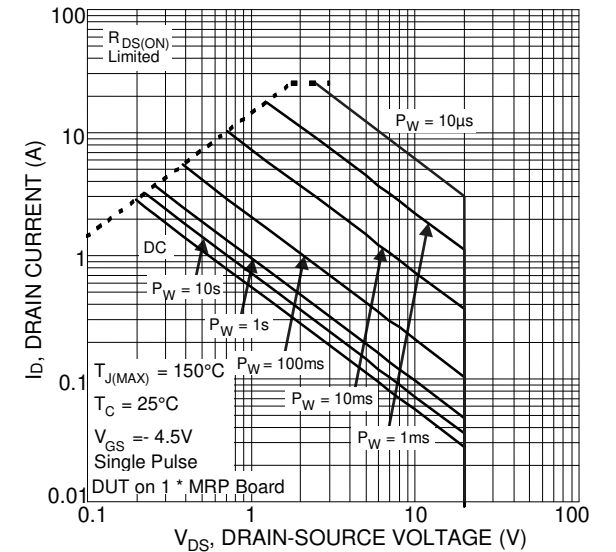


Figure 12 SOA, Safe Operation Area

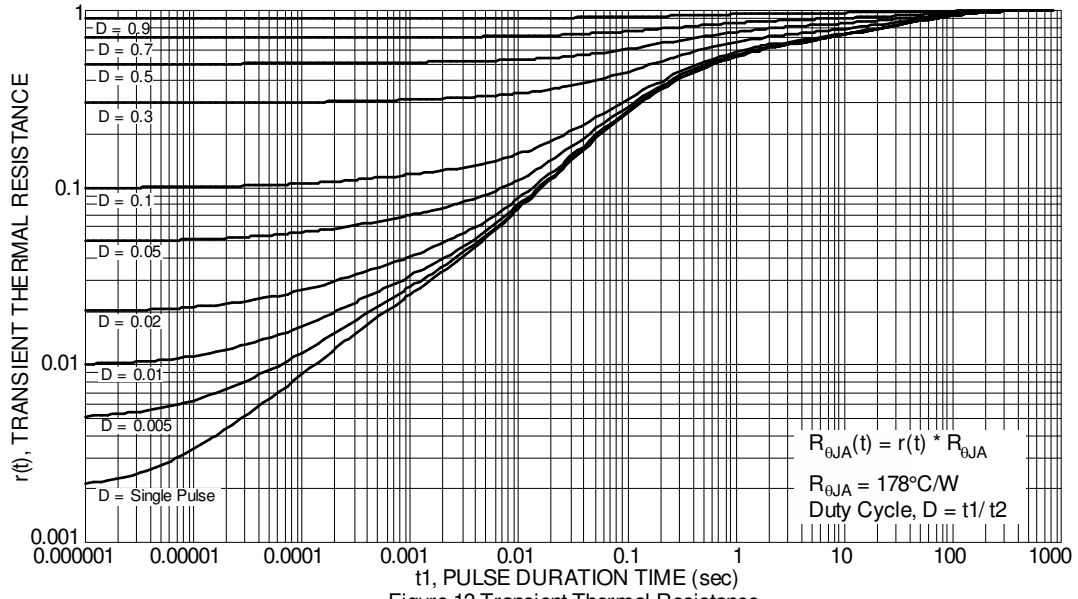
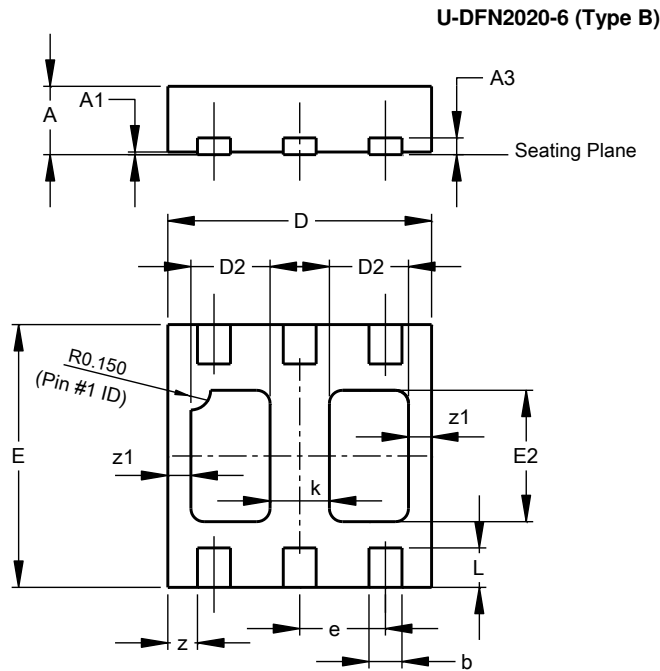


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

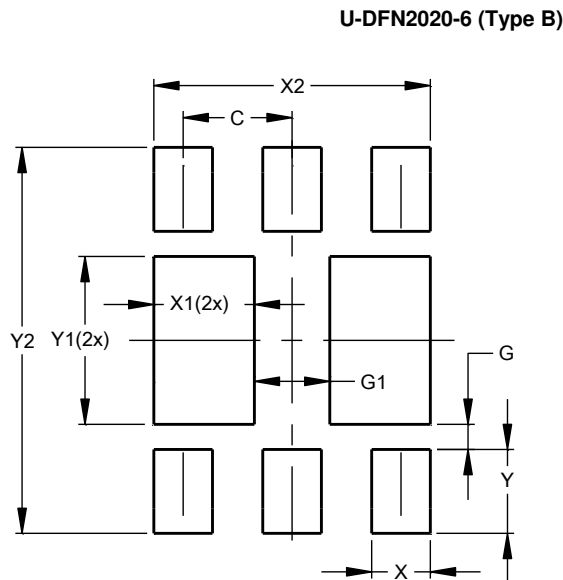
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



U-DFN2020-6 (Type B)			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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